

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

## Product Summary



$V_{DS}$	100	V
$I_D$	135	A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	3.9	mΩ

## Applications

- High Frequency Point-of-Load,Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch,Power Tool Application



## Absolute Maximum Ratings( $T_c=25^\circ C$ , unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D @ T_c = 25^\circ C$	135	A
Continuous Drain Current	$I_D @ T_c = 100^\circ C$	108	A
Pulsed Drain Current	$I_{DM}$	540	A
Single Pulse Avalanche Energy <sup>3</sup>	EAS	1156	mJ
Total Power Dissipation	$P_D @ T_c = 25^\circ C$	220	W
Storage Temperature Range	$T_{STG}$	-55 to 175	°C
Operating Junction Temperature Range	$T_J$	-55 to 175	°C

## Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Case <sup>1</sup>	$R_{\theta JC}$	---	0.68	°C/W

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}$ , $I_D=250\mu\text{A}$	100	---	---	V	
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}$ , $I_D=65\text{A}$	TO-220	---	3.65	3.9	$\text{m}\Omega$
		$V_{\text{GS}}=10\text{V}$ , $I_D=65\text{A}$	TO-263	---	3.5	3.9	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}$ , $I_D = 250\mu\text{A}$	2.0	3.0	4.0	V	
Drain-Source Leakage Current	$I_{\text{DSS}}$	$V_{\text{DS}}=100\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $T_J=25^\circ\text{C}$	---	---	1	$\mu\text{A}$	
Gate-Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 20\text{V}$ , $V_{\text{DS}}=0\text{V}$	---	---	$\pm 100$	nA	
Forward Transconductance	$g_{\text{fs}}$	$V_{\text{DS}}=5\text{V}$ , $I_D=65\text{A}$	---	90	---	S	
Gate Resistance	$R_g$	$V_{\text{DS}}=0\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	---	1.5	---	$\Omega$	
Total Gate Charge	$Q_g$	$V_{\text{DS}}=50\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $I_D=65\text{A}$	---	102	---	nC	
Gate-Source Charge	$Q_{\text{gs}}$		---	36	---		
Gate-Drain Charge	$Q_{\text{gd}}$		---	26	---		
Turn-On Delay Time	$T_{\text{d(on)}}$	$V_{\text{DD}}=50\text{V}$ , $I_D=65\text{A}$ , $V_{\text{GS}}=10\text{V}$ , $R_G=1.6\Omega$	---	20	---	ns	
Rise Time	$T_r$		---	11.5	---		
Turn-Off Delay Time	$T_{\text{d(off)}}$		---	48	---		
Fall Time	$T_f$		---	10	---		
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=50\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	---	6400	---	pF	
Output Capacitance	$C_{\text{oss}}$		---	585	---		
Reverse Transfer Capacitance	$C_{\text{rss}}$		---	26	---		

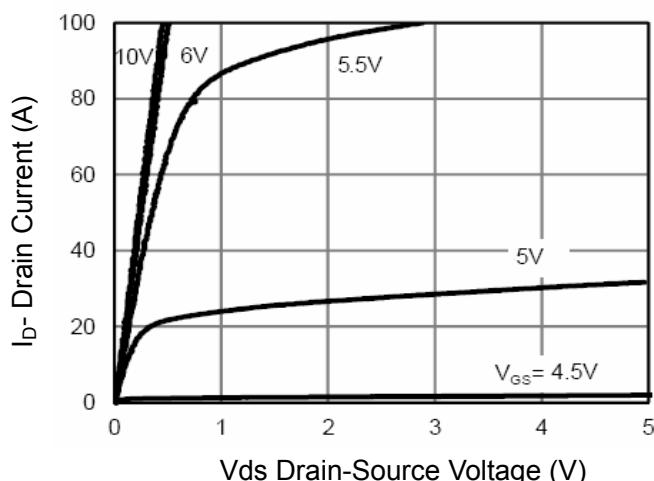
**Drain-Source Diode Characteristics**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current <sup>1</sup>	$I_s$		---	---	135	A
Diode Forward Voltage <sup>2</sup>	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}$ , $I_s=65\text{A}$ , $T_J=25^\circ\text{C}$	---	---	1.2	V
Reverse Recovery Time	$t_{\text{rr}}$	$I_F=65\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$ , $T_J=25^\circ\text{C}$	---	76	---	nS
	$Q_{\text{rr}}$		---	150	---	nC

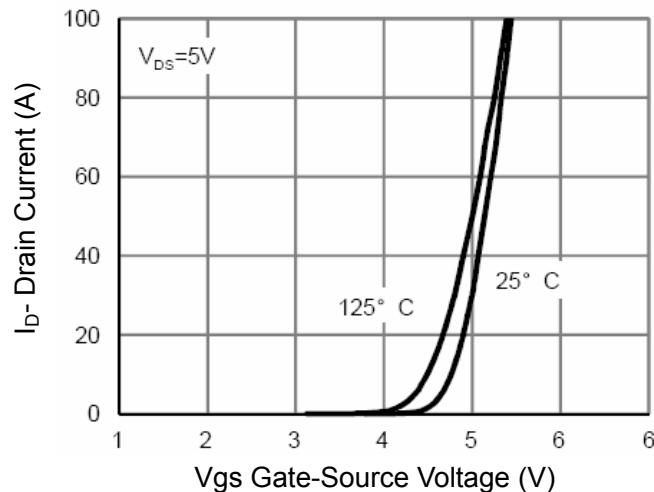
**Note:**

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu\text{s}$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{\text{DD}}=50\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $L=0.5\text{mH}$ , $R_G=25\Omega$

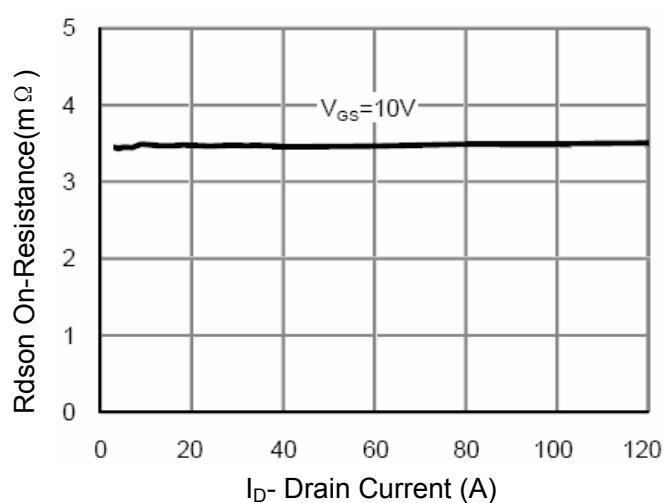
## Typical Characteristics



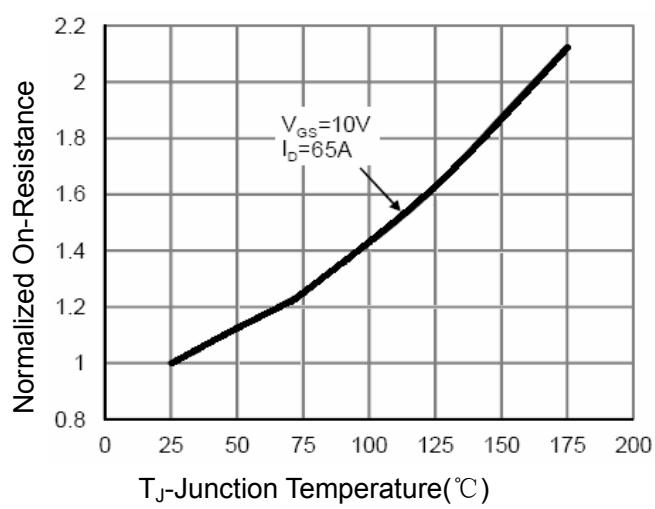
**Figure 1 Output Characteristics**



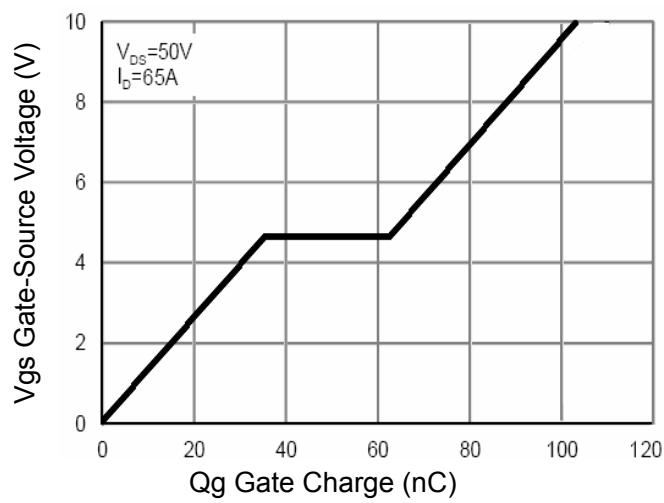
**Figure 2 Transfer Characteristics**



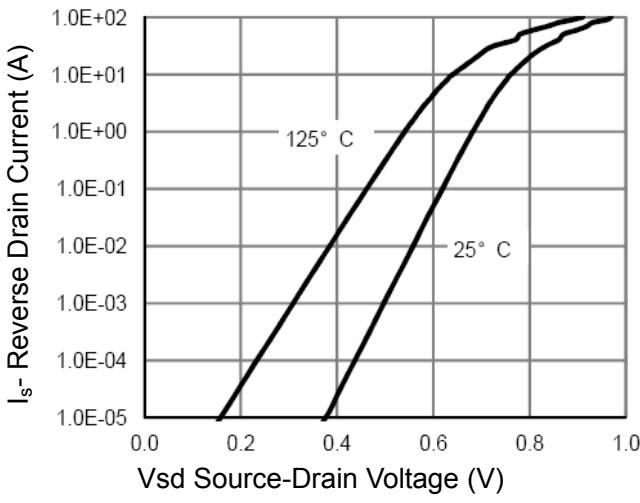
**Figure 3 Rdson- Drain Current**



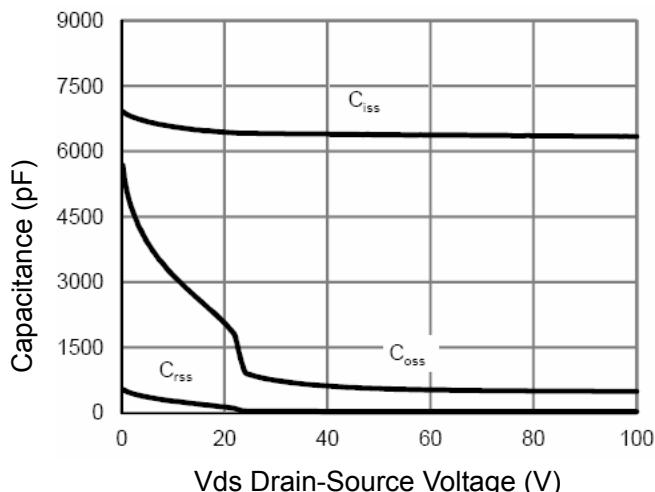
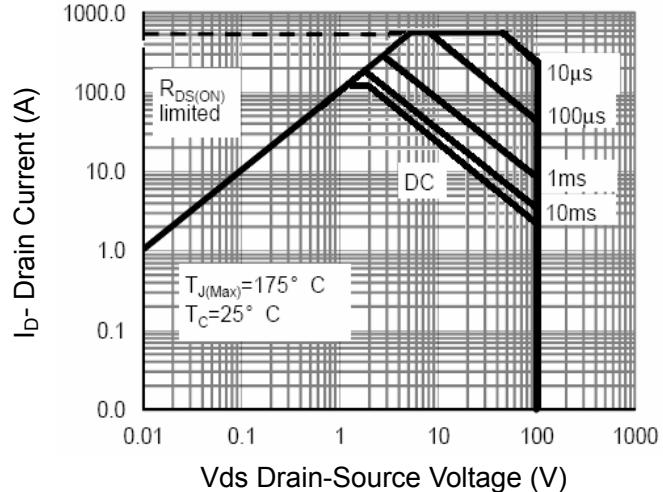
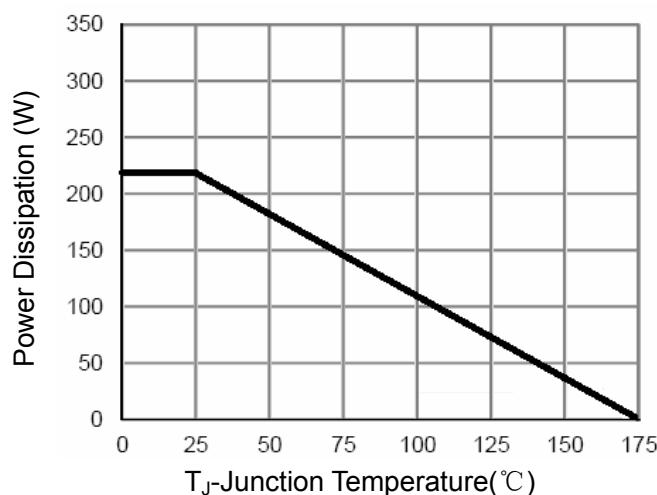
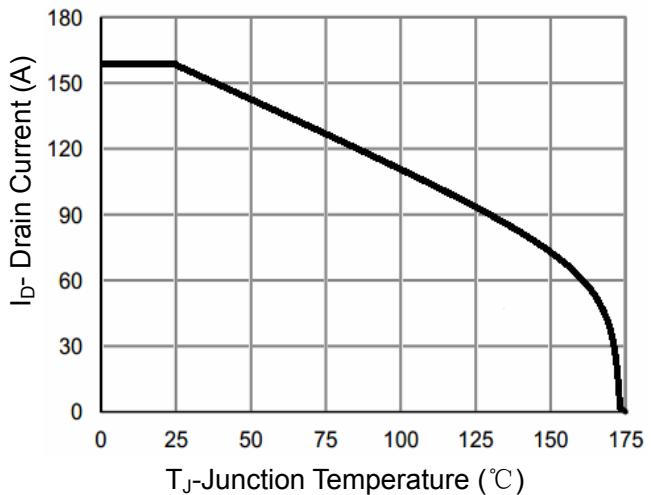
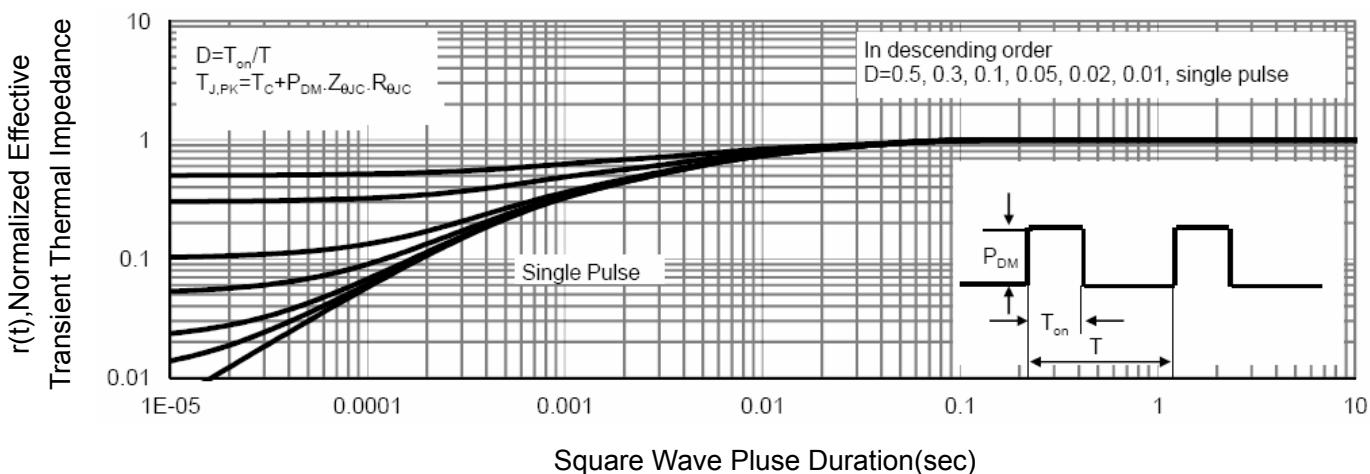
**Figure 4 Rdson-Junction Temperature**



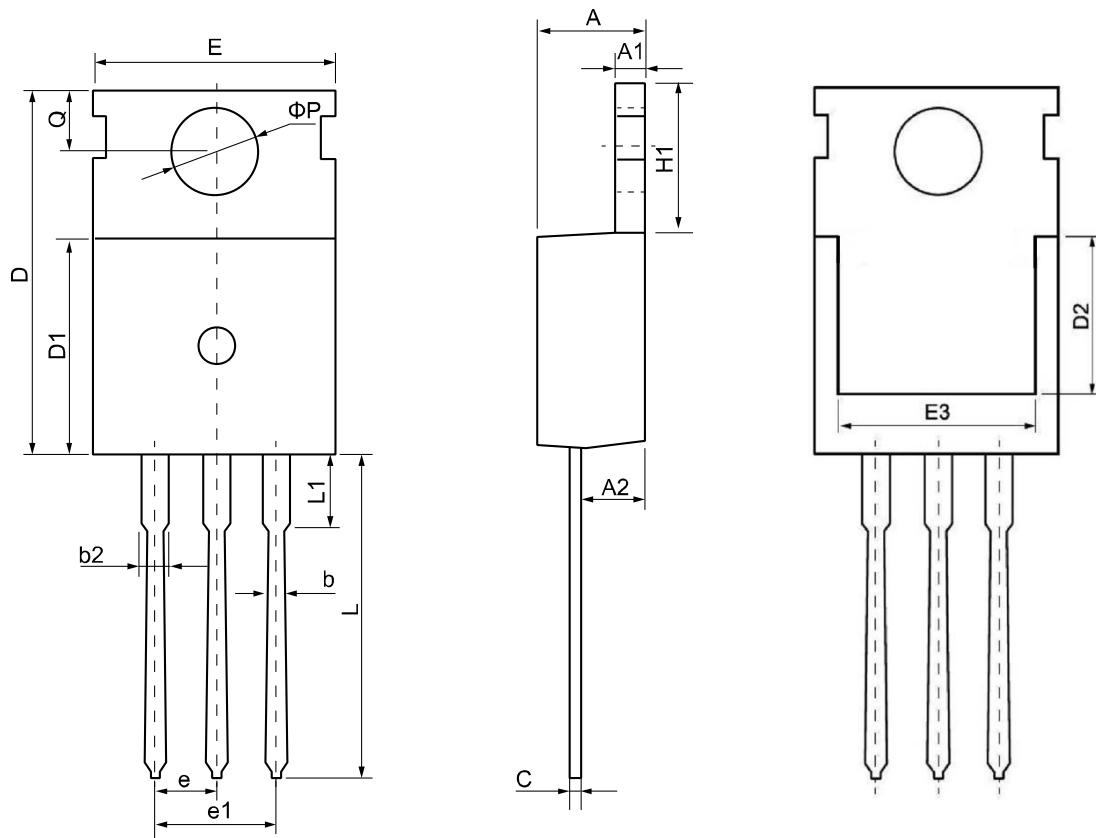
**Figure 5 Gate Charge**



**Figure 6 Source- Drain Diode Forward**

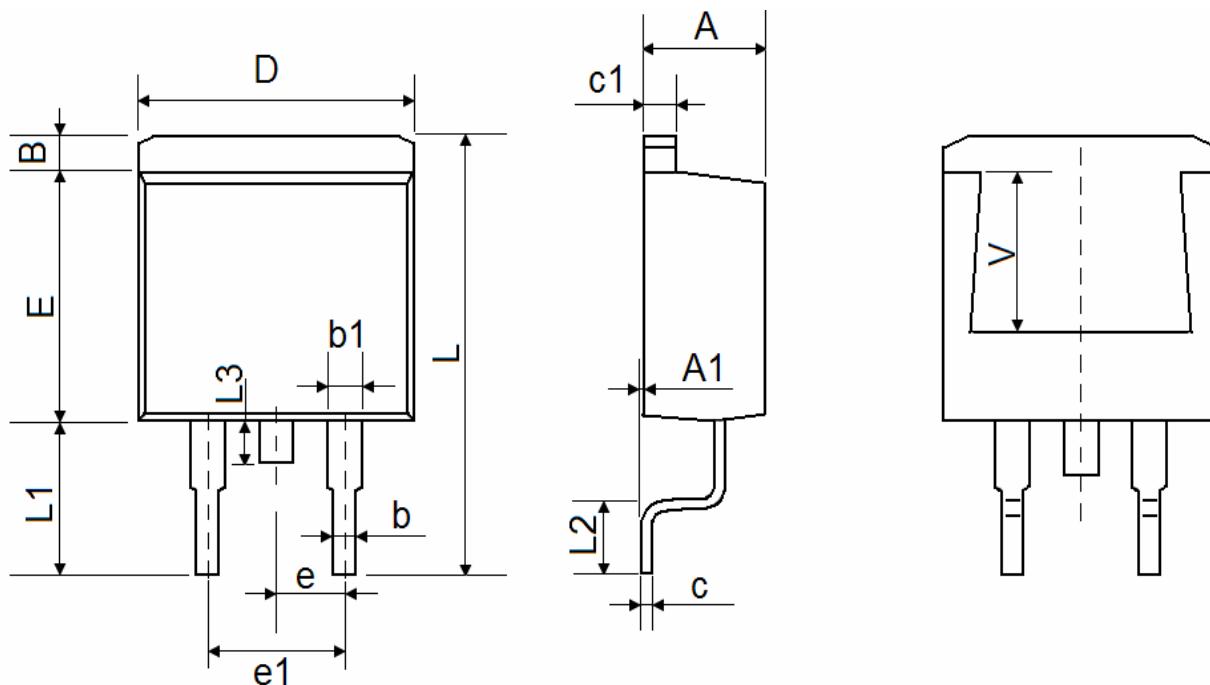

**Figure 7 Capacitance vs Vds**

**Figure 8 Safe Operation Area**

**Figure 9 Power De-rating**

**Figure 10 Current De-rating**

**Figure 11 Normalized Maximum Transient Thermal Impedance**

### TO-220 Package Outline Dimensions



<b>Symbol</b>	<b>Dimensions (unit:mm)</b>			<b>Symbol</b>	<b>Dimensions (unit:mm)</b>		
	<b>Min</b>	<b>Typ</b>	<b>Max</b>		<b>Min</b>	<b>Typ</b>	<b>Max</b>
<b>A</b>	4.30	4.55	4.75	<b>E</b>	9.65	10.00	10.25
<b>A1</b>	1.15	1.30	1.45	<b>E3</b>	7.00	--	--
<b>A2</b>	2.20	2.40	2.60	<b>e</b>	2.54 BSC		
<b>b</b>	0.70	0.80	0.95	<b>e1</b>	5.08 BSC		
<b>b2</b>	1.17	1.27	1.47	<b>H1</b>	6.30	6.50	6.80
<b>c</b>	0.40	0.50	0.65	<b>L</b>	12.70	13.50	14.10
<b>D</b>	15.30	15.60	15.90	<b>L1</b>	--	3.20	3.95
<b>D1</b>	8.90	9.10	9.35	<b>φP</b>	3.40	3.60	3.80
<b>D2</b>	5.50	--	--	<b>Q</b>	2.60	2.80	3.00

### TO-263 Package Outline Dimensions



<b>Symbol</b>	<b>Dimensions (unit:mm)</b>			<b>Symbol</b>	<b>Dimensions (unit:mm)</b>		
	<b>Min</b>	<b>Typ</b>	<b>Max</b>		<b>Min</b>	<b>Typ</b>	<b>Max</b>
<b>A</b>	4.40	4.55	4.70	<b>A1</b>	0.00	0.07	0.15
<b>B</b>	1.00	1.20	1.40	<b>b</b>	0.65	0.80	0.95
<b>b1</b>	1.10	1.15	1.37	<b>c</b>	0.30	0.40	0.53
<b>c1</b>	1.10	1.25	1.37	<b>D</b>	9.80	10.00	10.40
<b>E</b>	8.50	8.80	9.20	<b>e</b>	2.54 REF		
<b>e1</b>	4.90	5.10	5.40	<b>L</b>	14.80	15.20	15.70
<b>L1</b>	5.00	5.25	5.60	<b>L2</b>	2.05	2.45	2.80
<b>L3</b>	1.20	1.50	1.80	<b>V</b>	5.60 REF		